

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-7 (Canceled).

Claim 8 (Previously Presented): A semiconductor device comprising:

a plurality of external leads;

a die pad adjacent to the plurality of external leads;

a semiconductor chip mounted on the die pad and having a main electrode and a subelectrode smaller in area than the main electrode;

two inner leads configured to connect the main electrode and the subelectrode on the semiconductor chip to corresponding connecting pads of the plurality of external leads, respectively, the two inner leads each having a portion of a cut remainder of a tie bar.

Claim 9 (Original): The semiconductor device according to claim 8, wherein the tie bar is made smaller in thickness than other portions of the inner leads.

Claim 10 (Original): The semiconductor device according to claim 8, wherein the tie bar is provided midway on and between the external leads to which the two inner leads are connected.

Claim 11 (Previously Presented): The semiconductor device according to claim 8, wherein the tie bar comprises a plurality of sub tie bars connecting between the two inner leads and arranged separately.

Claim 12 (Previously Presented): The semiconductor device according to claim 8, wherein the die pad has a notch in a portion that faces a longitudinal side of the tie bar.

Claim 13 (Original): The semiconductor device according to claim 8, wherein the two inner leads have tie bar portions thereof formed higher than a top of the semiconductor chip.

Claim 14 (Original): The semiconductor device according to claim 8, wherein the semiconductor chip includes a MOSFET.

Claim 15 (Previously Presented): A semiconductor device comprising:

- a plurality of external leads;
- a first and a second die pad placed side by side adjacent to the plurality of external leads;
- a first and a second semiconductor chip each having a main electrode and a subelectrode smaller in area than the main electrode;
- two pairs of inner leads configured to connect the main electrode and the subelectrode on each of the first and the second semiconductor chip to corresponding connecting pads of the plurality of external leads, respectively, each pair of the inner leads having a portion of a cut remainder of a tie bar;
- a protruding lead portion formed vertically on one side of the first die pad which faces the second die pad; and
- a connecting lead portion formed integrally with one of the inner leads which is connected to the main electrode on the second semiconductor chip mounted on the second die

pad and having a notch engaged with the protruding lead portion so that the connecting lead portion and the protruded lead portion are electrically joined together.

Claim 16 (Original): The semiconductor device according to claim 15, wherein the protruding lead portion has a flat portion in an upper portion thereof which supports the connecting lead portion.

Claim 17 (Original): The semiconductor device according to claim 15, wherein each of the first and the second semiconductor chip includes a MOSFET and the first semiconductor chip further includes a Schottky diode connected in parallel with the MOSFET.

Claim 18 (Original): The semiconductor device according to claim 15, wherein the tie bar is made smaller in thickness than other portions of the inner leads.

Claim 19 (Original): The semiconductor device according to claim 15, wherein the tie bar is provided midway on and between the external leads to which the two inner leads are connected.

Claim 20 (Previously Presented): The semiconductor for device according to claim 15, wherein the die pad has a notch in a portion that faces a longitudinal side of the tie bar.

Claims 21-26 (Canceled).